

TO-92 Plastic-Encapsulate Transistors

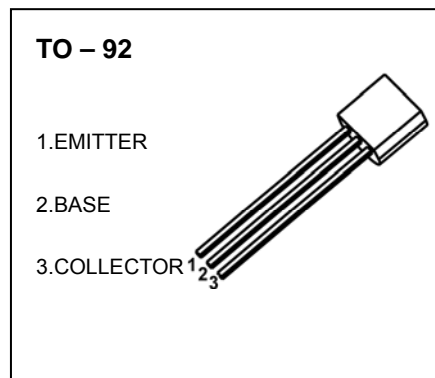
BC212 TRANSISTOR (PNP)

FEATURES

- General Purpose Switching and Amplification.

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.1	A
P _C	Collector Power Dissipation	0.35	W
R _{θJA}	Thermal Resistance From Junction To Ambient	357	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.01mA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-2mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.01mA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-30V, I _E =0			-15	nA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-15	nA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-2mA	BC212	140	600	
			BC212B	140	400	
			BC212C	350	600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-5mA			-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-5mA			-1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V, I _C =-2mA			-0.72	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz	200			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _C =0, f=1MHz			6	pF